# 2N7000

Preferred Device

## Small Signal MOSFET 200 mAmps, 60 Volts N-Channel TO-92

#### Features

- AEC Qualified
- PPAP Capable
- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	60	Vdc
Drain-Gate Voltage ( $R_{GS}$ = 1.0 M $\Omega$ )	V <sub>DGR</sub>	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I <sub>D</sub> I <sub>DM</sub>	200 500	mAdc
Total Power Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	350 2.8	mW mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

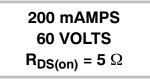
#### THERMAL CHARACTERISTICS

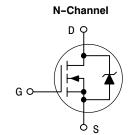
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	ΤL	300	°C

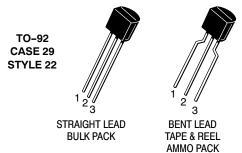
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



## **ON Semiconductor®**

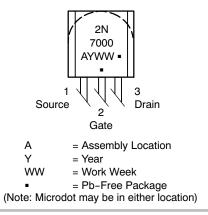






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MARKING DIAGRAM AND PIN ASSIGNMENT



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use

and best overall value.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## 2N7000

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$  unless otherwise noted)

C	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS	· · ·			•	
Drain-Source Breakdown Voltage	$V_{GS} = 0, I_D = 10 \ \mu Adc)$	V <sub>(BR)DSS</sub>	60	-	Vdc
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		1.0 1.0	μAdc mAdc	
Gate-Body Leakage Current, Forward (V <sub>GSF</sub> = 15 Vdc, V <sub>DS</sub> = 0)		I <sub>GSSF</sub>	-	-10	nAdc
ON CHARACTERISTICS (Note 1)	)				
Gate Threshold Voltage	$(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V <sub>GS(th)</sub>	0.8	3.0	Vdc
Static Drain-Source On-Resistan	r <sub>DS(on)</sub>		5.0 6.0	Ω	
Drain-Source On-Voltage	(V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 0.5 Adc) (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 75 mAdc)	V <sub>DS(on)</sub>		2.5 0.45	Vdc
On-State Drain Current	(V <sub>GS</sub> = 4.5 Vdc, V <sub>DS</sub> = 10 Vdc)	I <sub>d(on)</sub>	75	-	mAdc
Forward Transconductance	(V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 200 mAdc)	9fs	100	-	μmhos
DYNAMIC CHARACTERISTICS	·		•		
Input Capacitance		C <sub>iss</sub>	-	60	pF
Output Capacitance	(V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>oss</sub>	-	25	
Reverse Transfer Capacitance		C <sub>rss</sub>	-	5.0	
SWITCHING CHARACTERISTIC	S (Note 1)		•	·	·
Turn-On Delay Time	(V <sub>DD</sub> = 15 V, I <sub>D</sub> = 500 mA,	t <sub>on</sub>	-	10	ns
Turn-Off Delay Time	$R_{G}$ = 25 $\Omega$ , $R_{L}$ = 30 $\Omega$ , $V_{gen}$ = 10 V)	t <sub>off</sub>	-	10	

1. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

#### **ORDERING INFORMATION**

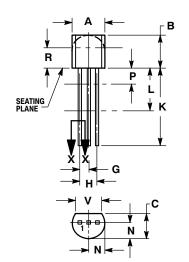
Device	Package	Shipping <sup>†</sup>
2N7000	TO-92	1000 Units / Bulk
2N7000G	TO-92 (Pb-Free)	1000 Units / Bulk
2N7000RLRA	TO-92	2000 Tape & Reel
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
2N7000RLRMG	TO-92 (Pb-Free)	2000 Tape & Ammo Box
2N7000RLRPG	TO-92 (Pb-Free)	2000 Tape & Ammo Box

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## 2N7000

### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** 





SECTION X-X

BENT LEAD

TAPE & REEL AMMO PACK

STRAIGHT LEAD **BULK PACK** 

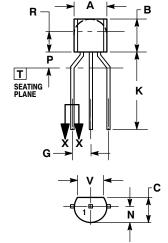
- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
V	3.43		

STYLE 22:	
PIN 1.	SOURCE
2.	GATE
3.	DRAIN





**SECTION X-X** 

2N7000/D